

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	336	MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact	USPAT	OR	ON	2005/04/02 15:08
L2	25	MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation	USPAT	OR	ON	2005/04/02 15:09
L3	0	MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and dpoed and polysilicon and isolation and conductive and gate	USPAT	OR	ON	2005/04/02 15:10
L4	21	MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and doped and polysilicon and isolation and conductive and gate	USPAT	OR	ON	2005/04/02 15:20
L5	1	MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and doped and polysilicon and isolation and conductive and gate and NMOS	USPAT	OR	ON	2005/04/02 15:12
L6	0	MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and (first adj region) and (second adj region) and (third adj region) and (fourth adj region)	USPAT	OR	ON	2005/04/02 15:13
L7	1	MOS and transistor and conductivity and n-type and p-type and region and mask and trench and metal and plug and contact and crystallographic and orientation and first and second and third and fourth	USPAT	OR	ON	2005/04/02 15:17

L8	1	"6075276".PN.	USPAT; USOCR	OR	ON	2005/04/02 15:14
L9	1	"4484206".PN.	USPAT; USOCR	OR	ON	2005/04/02 15:14
L10	1	"4419681".PN.	USPAT; USOCR	OR	ON	2005/04/02 15:15
L11	1	("6639031").PN.	USPAT	OR	OFF	2005/04/02 15:17
L12	432	MOS and transistor and (first adj region) and (second adj region) and (third adj region) and (fourth adj region)	USPAT	OR	ON	2005/04/02 15:21
L13	8	MOS and transistor and (first adj region) and (second adj region) and (third adj region) and (fourth adj region) and conductivity and crystallographic and orientation	USPAT	OR	ON	2005/04/02 15:29
L14	628	257/69	USPAT	OR	ON	2005/04/02 15:29
L15	1175	257/192	USPAT	OR	ON	2005/04/02 15:30
L16	787	257/197	USPAT	OR	ON	2005/04/02 15:30
L17	339	257/213	USPAT	OR	ON	2005/04/02 15:30
L18	950	257/288	USPAT	OR	ON	2005/04/02 15:30
L19	882	257/324	USPAT	OR	ON	2005/04/02 15:30
L20	3165	257/347	USPAT	OR	ON	2005/04/02 15:30